

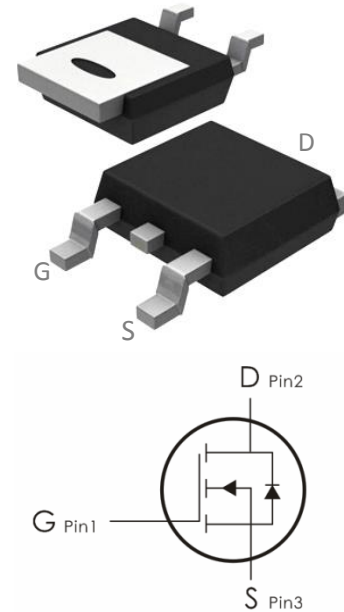
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=20V, I_D=60A, R_{DS(on)} < 6m\Omega @ V_{GS}=4.5V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current- $T_C=25^\circ C$	60	A
	Continuous Drain Current- $T_C=100^\circ C$	42	
	Pulsed Drain Current ¹	210	
E_{AS}	Single Pulse Avalanche Energy	200	mJ
P_D	Power Dissipation, $T_C=25^\circ C$	60	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.1	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	---	

Electrical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	20	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=20V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	0.5	0.75	1.0	V
$R_{DS(on)}$	Drain-Source On Resistance ³	$V_{GS}=4.5V, I_D=20A$	---	4.8	6	$\text{m}\Omega$
		$V_{GS}=2.5V, I_D=15A$	---	6.2	9	
G_{FS}	Forward Transconductance	$V_{DS}=10V, I_D=20A$	15	---	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, f=1\text{MHz}$	---	2000	---	pF
C_{oss}	Output Capacitance		---	500	---	
C_{rss}	Reverse Transfer Capacitance		---	200	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time ³	$V_{DD}=10V, I_D=2A,$ $V_{GS}=4.5V, R_G=3\Omega$	---	6.4	---	ns
t_r	Rise Time ^{2,3}		---	17.2	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	29.6	---	ns
t_f	Fall Time ^{2,3}		---	16.8	---	ns
Q_g	Total Gate Charge ³	$V_{GS}=10V, V_{DS}=10V,$ $I_D=20A$	---	27	30	nC
Q_{gs}	Gate-Source Charge		---	6.5	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	6.4	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage ³	$V_{GS}=0V, I_S=10A$	---	---	1.2	V

LS	Diode Forward Current(Note 2)		---	---	60	A
Trr	Reverse Recovery Time	T _J = 25°C, I _F = 20A di/dt = 100A/μs ^(Note3)	---	25	---	Ns
Qrr	Reverse Recovery Charge		---	24	---	Nc

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=10V, V_G=10V, L=0.5mH, R_G=25Ω,

Typical Characteristics: (T_C=25°C unless otherwise noted)

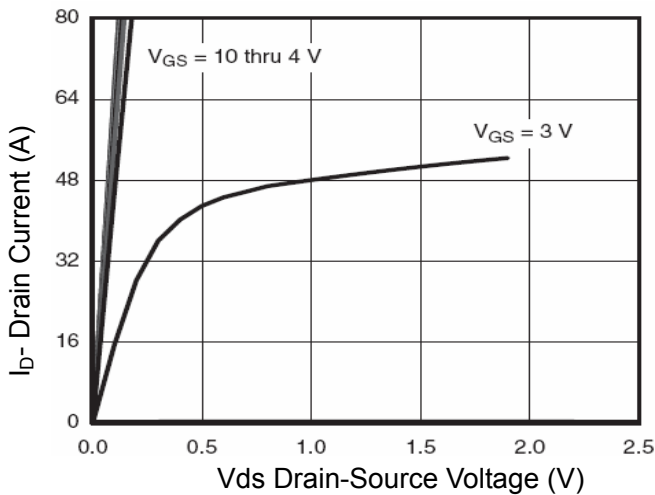


Figure 1 Output Characteristics

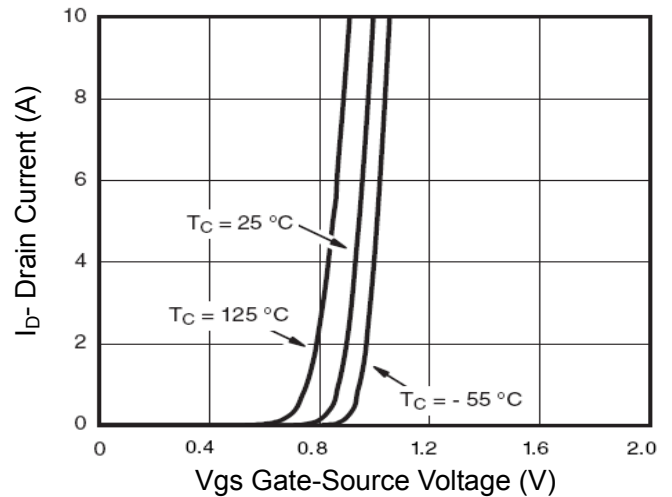


Figure 2 Transfer Characteristics

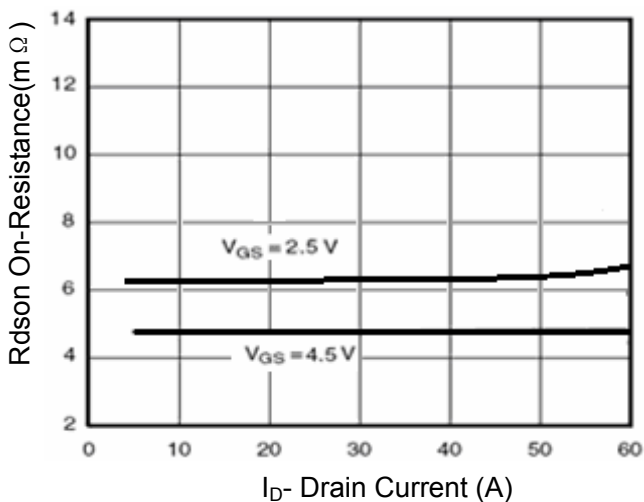


Figure 3 Rdson- Drain Current

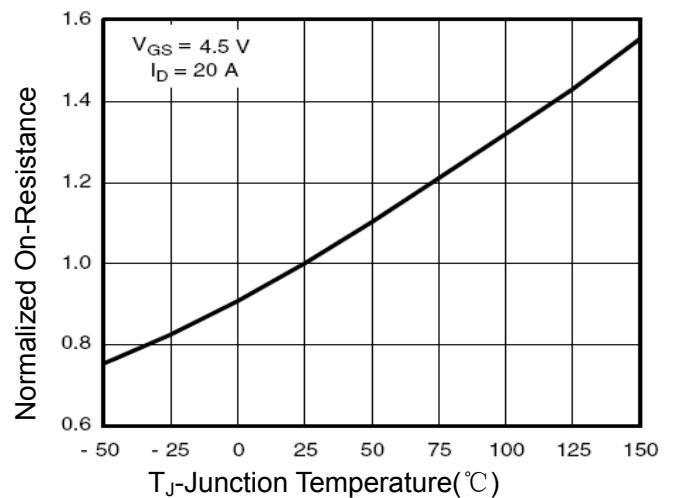


Figure 4 Rdson-Junction Temperature

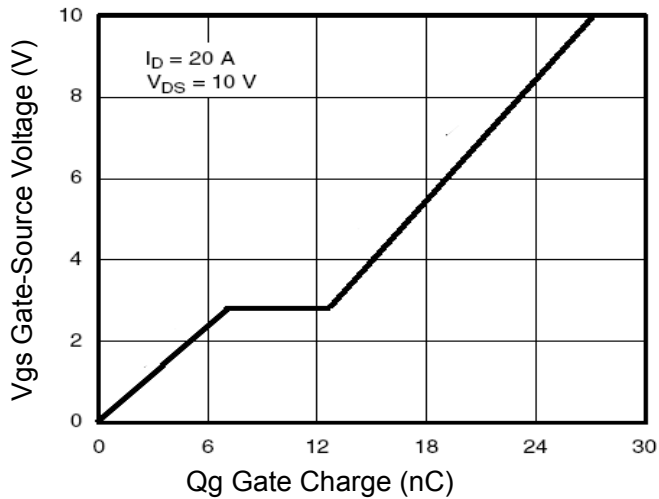


Figure 5 Gate Charge

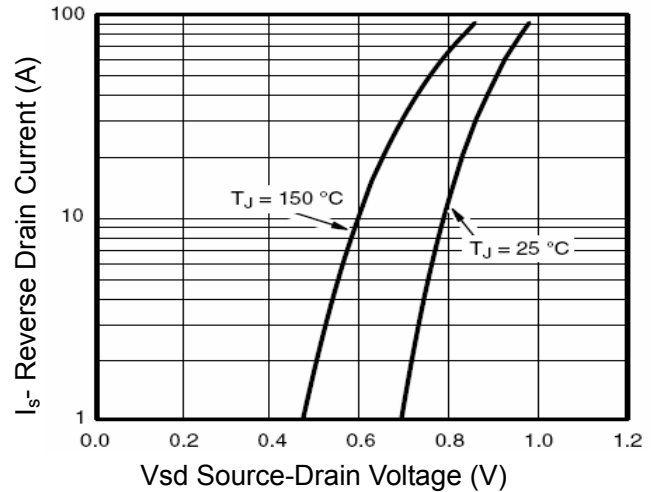


Figure 6 Source- Drain Diode Forward

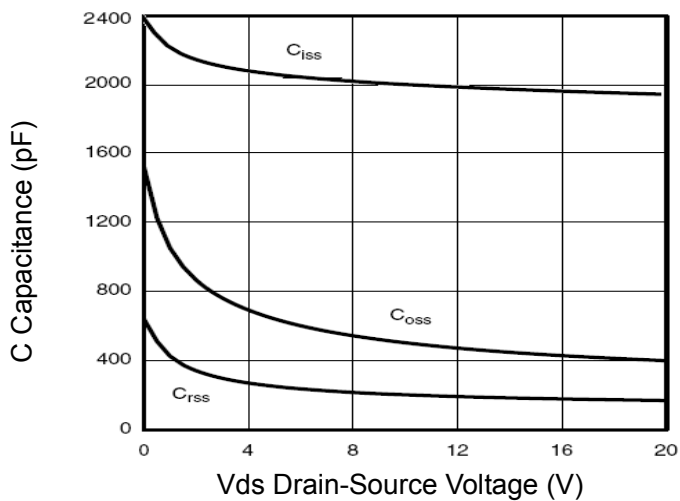


Figure 7 Capacitance vs Vds

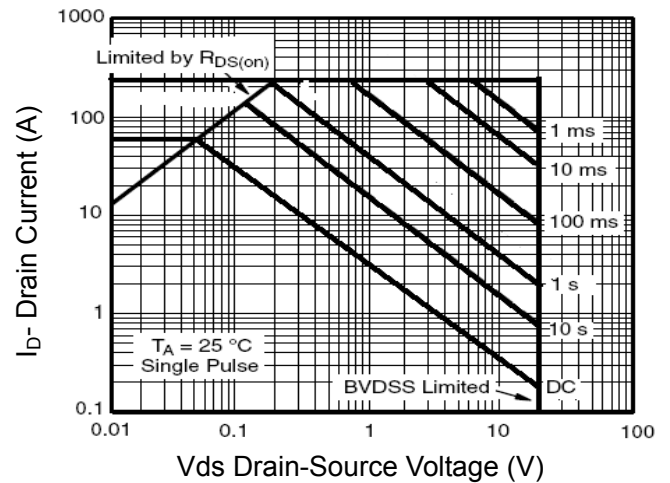


Figure 8 Safe Operation Area

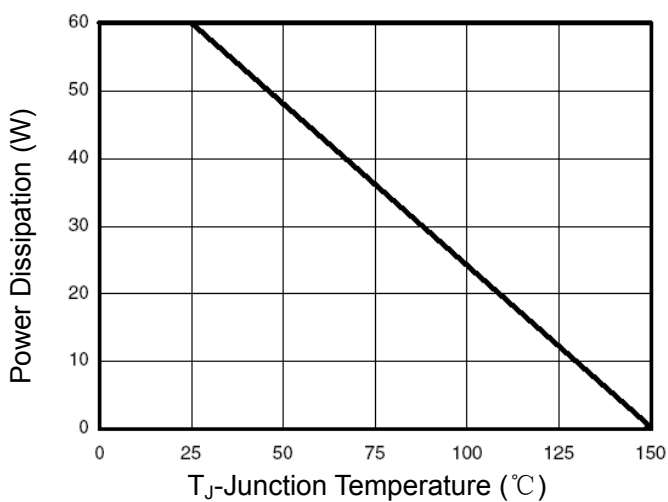


Figure 9 Power De-rating

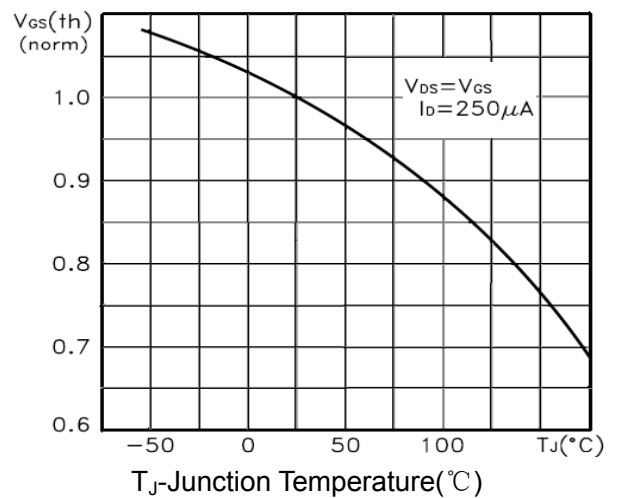


Figure 10 VGS(th) vs Junction Temperature

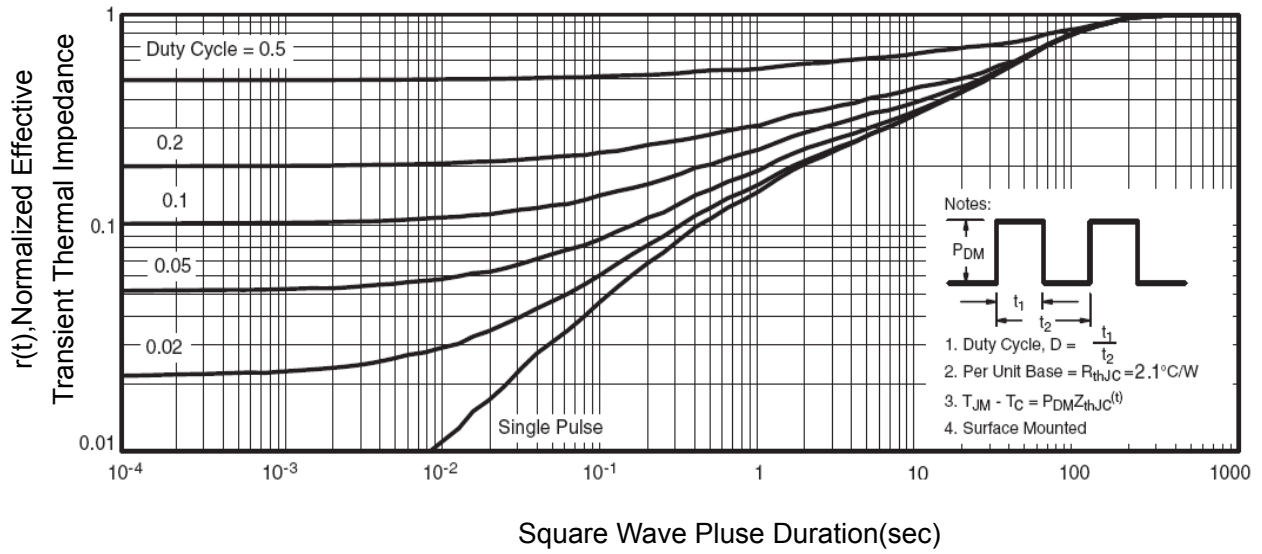


Figure 11 Normalized Maximum Transient Thermal Impedance



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